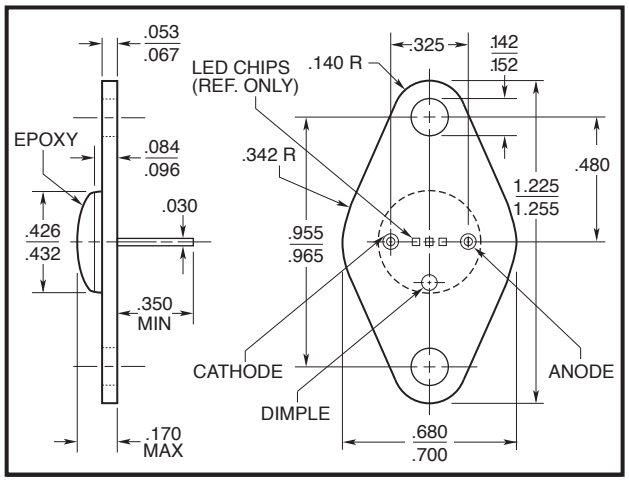

FEATURES

- Super high power output
- 880nm peak emission
- Three chips connected in series
- TO-66 header for good heat dissipation
- 100% tested for power output
- Electrically isolated case

All surfaces are gold plated. Dimensions are nominal values in inches unless otherwise specified.

RoHS

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Total Power Output, P_o	I_F = 300mA I_F = 8A	150	170 3500		mW
Peak Emission Wavelength, λ_P	I_F = 50mA		880		nm
Spectral Bandwidth at 50%, $\Delta\lambda$			80		nm
Half Intensity Beam Angle, θ			120		Deg
Forward Voltage, V_F	I_F = 300mA		4.5	5	Volts
Reverse Breakdown Voltage, V_R	I_R = 10µA	5	30		Volts
Capacitance, C	V_R = 0V		30		pF
Rise Time			1		µsec
Fall Time			1		µsec

ABSOLUTE MAXIMUM RATINGS AT 25°C CASE

Power Dissipation[1]	2W
Continuous Forward Current	400mA
Peak Forward Current (10µs, 400Hz)[2]	8A
Reverse Voltage	5V
Lead Soldering Temperature (1/16" from case for 10sec)	260°C

[1]Derate per Thermal Derating Curve above 25°C
[2]Derate linearly above 25°C

THERMAL PARAMETERS

Storage and Operating Temperature Range	-55°C to 100°C
Maximum Junction Temperature	100°C
Thermal Resistance, R_{THJA}[1]	60°C/W Typical
Thermal Resistance, R_{THJA}[2]	16°C/W Typical

[1]Heat transfer minimized by measuring in still air with minimum heat conducting through leads
[2]Air circulating at a rapid rate to keep case temperature at 25°C

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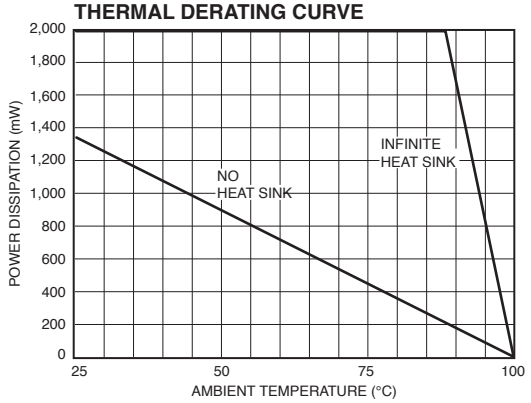
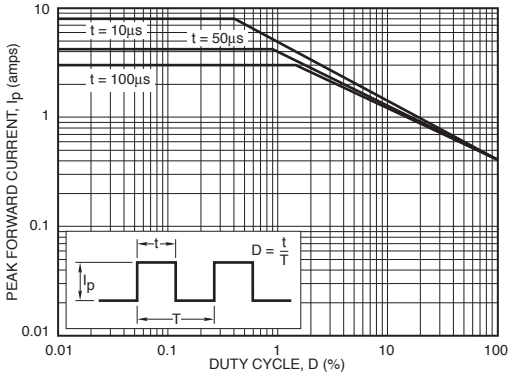
Revision February 26, 2013

MAXIMUM RATINGS

THERMAL DERATING CURVE

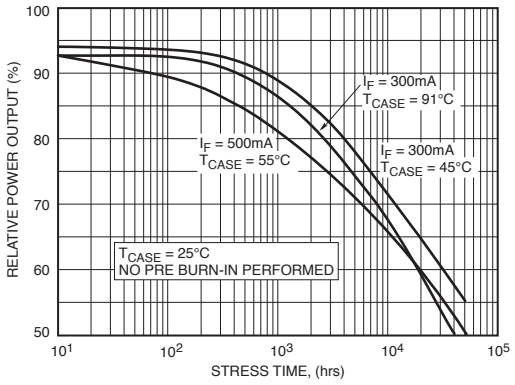


MAXIMUM PEAK PULSE CURRENT

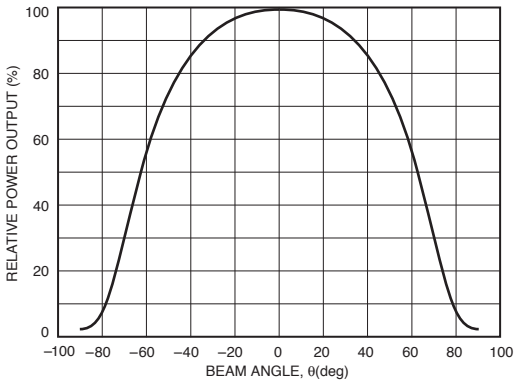


TYPICAL CHARACTERISTICS

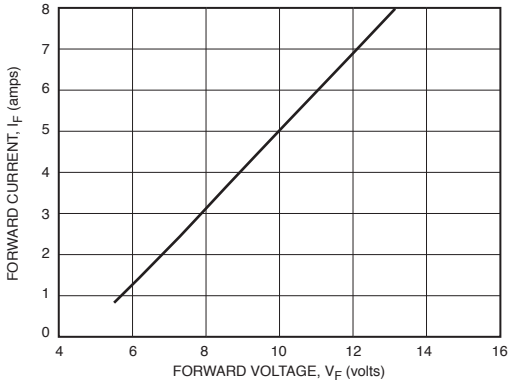
DEGRADATION CURVE



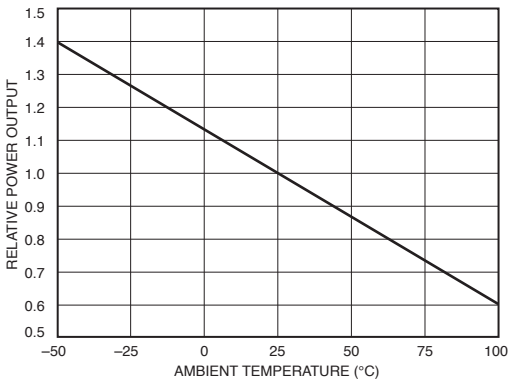
RADIATION PATTERN



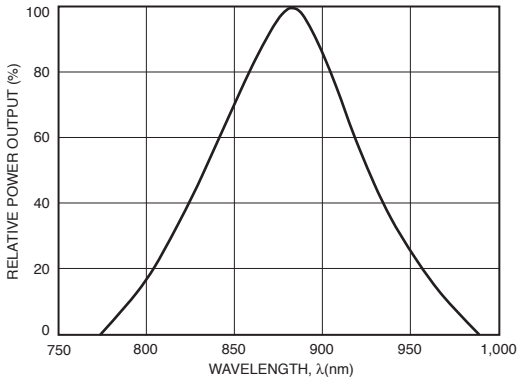
FORWARD I-V CHARACTERISTICS



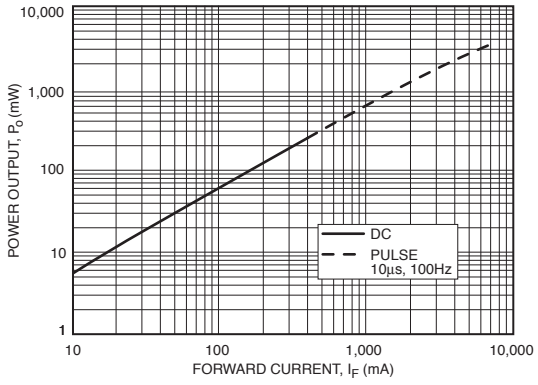
POWER OUTPUT vs TEMPERATURE



SPECTRAL OUTPUT



POWER OUTPUT vs FORWARD CURRENT



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